

**Silicon PNP transistor epitaxial type
AP964**

[Applications]

High voltage switching and amplifier

[Feature]

High voltage VCEO= -400V

Small collector output capacitance Cob= 2.5pF (Typ.) at VCB= -20V

NPN complementary pair with CP964

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-400	V
Collector-emitter voltage	VCEO	-400	V
Emitter-base voltage	VEBO	-7	V
Collector current	IC	-300	mA
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	-400	-	-	V	IC= -100uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	-400	-	-	V	IC= -1mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	-7	-	-	V	IE= -100uA, IC= 0A
Collector cut-off current	ICBO	-	-	-0.5	uA	VCB= -400V, IE= 0A
DC current gain 1	hFE 1	40	-	-	-	VCE= -10V, IC= -4mA
DC current gain 2	hFE 2	70	-	200	-	VCE= -10V, IC= -20mA
Collector-emitter saturation voltage	VCE(sat)	-	-	-0.5	V	IC= -50mA, IB= -5mA
Base-emitter saturation voltage	VBE(sat)	-	-	-1.1	V	IC= -50mA, IB= -5mA
Transition frequency	fT	50	-	-	MHz	VCE= -10V, IE= 20mA
Collector output capacitance	Cob	-	-	7	pF	VCB= -20V, f = 1MHz, IE= 0A

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

